

## MEMORY CELL STRINGS

### Abstract of the Disclosure

A method for performing a read operation from a magnetic random access memory (MRAM) cell in a memory cell string is provided. The method includes applying a constant current through the memory cell string, measuring a first voltage across the memory cell string, applying a write sense current across the MRAM cell, measuring a second voltage across the memory cell string, and determining whether the first voltage differs from the second voltage.